

PD57018 PD57018S RF POWER TRANSISTORS

The LdmoST Plastic FAMILY

N-CHANNEL ENHANCEMENT-MODE LATERAL **MOSFETs**

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- POUT = 18 W with 14 dB gain @ 960 MHz / 28V
- NEW RF PLASTIC PACKAGE

DESCRIPTION

The PD57018 is a common source N-Channel, enhancement-mode, lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 28V in common source mode at frequencies of up to 1GHz. PD57018 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the first true SMD plastic RF power package, PowerSO-10RF. PD57018's superior linearity performance makes it an ideal solution for base station applications.

The PowerSO-10 plastic package, designed to offer high reliability, is the first ST JEDEC approved, high power SMD package. It has been specially optimized for RF needs and offers excellent RF performances and ease of assembly.



Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-Source Voltage	65	V
V _{GS}	Gate-Source Voltage	±20	V
۱ _D	Drain Current	2.5	А
PDISS	Power Dissipation (@ Tc = $70 {}^{\circ}C$)	31.7	W
Tj	Max. Operating Junction Temperature	165	0C
T _{STG}	Storage Temperature	-65 to 175	0C

ABSOLUTE MAXIMUM RATINGS(TCASE = 25 °C)

THERMAL DATA (T_{CASE} = 70 °C)

R _{th(j-c)}	Junction-Case Thermal Resistance	3.0	⁰ C/W
Jun 2000			1/4

PD57018 PD57018S

ELECTRICAL SPECIFICATION(T_{CASE} = 25 °C)

STATIC

Symbol	Parameter		Min.	Тур.	Max.	Unit	
V _{(BR)DSS}	$V_{GS} = 0 V$	I _{DS} = 10 mA		65			V
I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 28 V				1	μΑ
I _{GSS}	$V_{GS} = 20 V$	$V_{DS} = 0 V$				1	μΑ
V _{GS(Q)}	V _{DS} = 28 V	I _D = 50 mA		2.0		5.0	V
V _{DS(ON)}	$V_{GS} = 10 V$	I _D = 1 A			0.3		V
g fs	V _{DS} = 10 V	I _D = 1 A					mho
Ciss	$V_{GS} = 0 V$	V _{DS} = 28 V	f = 1 MHz		36		pF
C _{OSS}	$V_{GS} = 0 V$	$V_{DS} = 28 V$	f = 1 MHz		19		pF
C _{RSS}	$V_{GS} = 0 V$	V _{DS} = 28 V	f = 1 MHz		0.9		pF

DYNAMIC

Symbol	Parameter			Тур.	Max.	Unit
Pout	V _{DD} = 28 V f = 960 MHz	_{DQ} = 50 mA	18			W
G _{PS}	$V_{DD} = 28 V f = 960 MHz F$	$P_{OUT} = 18 \text{ W}$ $I_{DQ} = 50 \text{ mA}$	14	15		dB
ηD	$V_{DD} = 28 V f = 960 MHz F$	$P_{OUT} = 18 \text{ W}$ $I_{DQ} = 50 \text{ mA}$	50	60		%
LOAD Mismatch	V _{DD} = 2 V f = 960 MHz F ALL PHASE ANGLES	P _{OUT} = 18 W I _{DQ} = 50 mA	10:1			VSWR



57



PowerSO-10RF (Straight Lead) MECHANICAL DATA

PowerSO-10RF (Formed Lead) MECHANICAL DATA



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

All other names are the property of their respective owners.

STMicroelectronics GROUP OF COMPANIES Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco -Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

http://www.st.com

